Yuanlin Shi

List of Publications by Year
in descending order

24 papers	599 citations	567281 15 h-index	610901 24 g-index
25 all docs	25 docs citations	25 times ranked	762 citing authors

#	Article	IF	Citations
1	Graphene/Organic Semiconductor Heterojunction Phototransistors with Broadband and Biâ€directional Photoresponse. Advanced Materials, 2018, 30, e1804020.	21.0	103
2	High thermochromic performance of Fe/Mg co-doped VO₂ thin films for smart window applications. Journal of Materials Chemistry C, 2018, 6, 6502-6509.	5.5	72
3	Three-Dimensional Topological Insulator Bi₂Te₃/Organic Thin Film Heterojunction Photodetector with Fast and Wideband Response from 450 to 3500 Nanometers. ACS Nano, 2019, 13, 755-763.	14.6	68
4	Ultrahigh Stability 3D TI Bi₂Se₃/MoO₃ Thin Film Heterojunction Infrared Photodetector at Optical Communication Waveband. Advanced Functional Materials, 2020, 30, 1909659.	14.9	50
5	Light-modulated vertical heterojunction phototransistors with distinct logical photocurrents. Light: Science and Applications, 2020, 9, 167.	16.6	40
6	Enhancement of VO2 thermochromic properties by Si doping. Surface and Coatings Technology, 2015, 276, 248-253.	4.8	37
7	Metalâ€“insulator transition properties of sputtered silicon-doped and un-doped vanadium dioxide films at terahertz range. Applied Surface Science, 2015, 331, 92-97.	6.1	35
8	Ultraviolet to Long-Wave Infrared Photodetectors Based on a Three-Dimensional Dirac Semimetal/Organic Thin Film Heterojunction. Journal of Physical Chemistry Letters, 2019, 10, 3914-3921.	4.6	29
9	Effect of Fe doping on thermochromic properties of VO2 films. Journal of Materials Science: Materials in Electronics, 2018, 29, 5501-5508.	2.2	25
10	Polarimetric Three-Dimensional Topological Insulators/Organics Thin Film Heterojunction Photodetectors. ACS Nano, 2019, 13, 10810-10817.	14.6	20
11	Improvement of phase transition properties of magnetron sputtered W-doped VO2 films by post-annealing approach. Journal of Materials Science: Materials in Electronics, 2020, 31, 4150-4160.	2.2	19
12	A silicon-based PbSe quantum dot near-infrared photodetector with spectral selectivity. Nanoscale, 2021, 13, 12306-12313.	5.6	19
13	Preparation and phase transition properties of nanostructured zirconium-doped vanadium oxide films by reactive magnetron sputtering. Thin Solid Films, 2014, 568, 63-69.	1.8	17
14	Silicon-based PbS-CQDs infrared photodetector with high sensitivity and fast response. Nanotechnology, 2020, 31, 485206.	2.6	17
15	Electrically tunable mid-infrared antennas based on VO₂. Journal of Modern Optics, 2018, 65, 1809-1816.	1.3	15
16	A 3D topological Dirac semimetal/MoO₃ thin film heterojunction infrared photodetector with a current reversal phenomenon. Journal of Materials Chemistry C, 2020, 8, 16024-16031.	5.5	10
17	Design and preparation of a VO2-based high-performance metamaterial for smart windows. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	6
18	Type-III organic/two-dimensional multi-layered phototransistors with promoted operation speed at the communication band. Journal of Materials Chemistry C, 2021, 9, 13963-13971.	5.5	6

#	Article	IF	Citations
19	Near-infrared heterojunction field modulated phototransistors with distinct photodetection/photostorage switching features for artificial visuals. Journal of Materials Chemistry C, 2022, 10, 9198-9207.	5.5	3
20	Phototransistors: Graphene/Organic Semiconductor Heterojunction Phototransistors with Broadband and Bi-directional Photoresponse (Adv. Mater. 49/2018). Advanced Materials, 2018, 30, 1870379.	21.0	2
21	Far-IR transmittance and metalâ€“insulator phase transition properties of VO2 films using Al2O3 as buffer layer. Journal of Materials Science: Materials in Electronics, 2019, 30, 6448-6458.	2.2	2
22	Effects of copper doping of vanadium dioxide films on DC and terahertz conductivity. Journal of Applied Physics, 2020, 127, 033103.	2.5	2
23	Effect of low-valence vanadium buffer layer on the properties of vanadium oxide film. Journal of Materials Science: Materials in Electronics, 2020, 31, 1715-1721.	2.2	1
24	Photodetectors: Ultrahigh Stability 3D TI Bi₂Se₃/MoO₃ Thin Film Heterojunction Infrared Photodetector at Optical Communication Waveband (Adv. Funct. Mater.) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	14.9	1